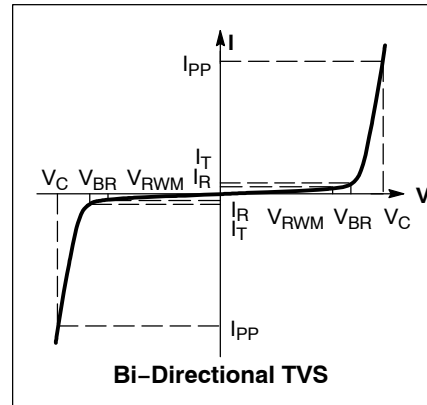


## P6SMB11CAT3 Series

### ELECTRICAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
V <sub>RWM</sub>	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
ΘV <sub>BR</sub>	Maximum Temperature Coefficient of V <sub>BR</sub>



### ELECTRICAL CHARACTERISTICS (Devices listed in bold, italic are ON Semiconductor Preferred devices.)

Device*	Device Marking	V <sub>RWM</sub> (Note 4)	I <sub>R</sub> @ V <sub>RWM</sub>	Breakdown Voltage				V <sub>C</sub> @ I <sub>PP</sub> (Note 6)		ΘV <sub>BR</sub>	C <sub>typ</sub> (Note 7)
				V <sub>BR</sub> Volts (Note 5)			@ I <sub>T</sub>	V <sub>C</sub>	I <sub>PP</sub>		
		Volts	μA	Min	Nom	Max	mA	Volts	Amps	%/°C	pF
P6SMB11CAT3, G	11C	9.4	5	10.5	11.05	11.6	1	15.6	38	0.075	865
P6SMB12CAT3, G	12C	10.2	5	11.4	12	12.6	1	16.7	36	0.078	800
P6SMB13CAT3, G	13C	11.1	5	12.4	13.05	13.7	1	18.2	33	0.081	740
P6SMB15CAT3, G	15C	12.8	5	14.3	15.05	15.8	1	21.2	28	0.084	645
P6SMB16CAT3, G	16C	13.6	5	15.2	16	16.8	1	22.5	27	0.086	610
P6SMB18CAT3, G	18C	15.3	5	17.1	18	18.9	1	25.2	24	0.088	545
P6SMB20CAT3, G	20C	17.1	5	19	20	21	1	27.7	22	0.09	490
P6SMB22CAT3, G	22C	18.8	5	20.9	22	23.1	1	30.6	20	0.09	450
P6SMB24CAT3, G	24C	20.5	5	22.8	24	25.2	1	33.2	18	0.094	415
P6SMB27CAT3, G	27C	23.1	5	25.7	27.05	28.4	1	37.5	16	0.096	370
P6SMB30CAT3, G	30C	25.6	5	28.5	30	31.5	1	41.4	14.4	0.097	335
<b>P6SMB33CAT3, G</b>	<b>33C</b>	<b>28.2</b>	<b>5</b>	<b>31.4</b>	<b>33.05</b>	<b>34.7</b>	<b>1</b>	<b>45.7</b>	<b>13.2</b>	<b>0.098</b>	<b>305</b>
P6SMB36CAT3, G	36C	30.8	5	34.2	36	37.8	1	49.9	12	0.099	280
P6SMB39CAT3, G	39C	33.3	5	37.1	39.05	41	1	53.9	11.2	0.1	260
P6SMB43CAT3, G	43C	36.8	5	40.9	43.05	45.2	1	59.3	10.1	0.101	240
P6SMB47CAT3, G	47C	40.2	5	44.7	47.05	49.4	1	64.8	9.3	0.101	220
P6SMB51CAT3, G	51C	43.6	5	48.5	51.05	53.6	1	70.1	8.6	0.102	205
P6SMB56CAT3, G	56C	47.8	5	53.2	56	58.8	1	77	7.8	0.103	185
P6SMB62CAT3, G	62C	53	5	58.9	62	65.1	1	85	7.1	0.104	170
P6SMB68CAT3, G	68C	58.1	5	64.6	68	71.4	1	92	6.5	0.104	155
P6SMB75CAT3, G	75C	64.1	5	71.3	75.05	78.8	1	103	5.8	0.105	140
P6SMB82CAT3, G	82C	70.1	5	77.9	82	86.1	1	113	5.3	0.105	130
P6SMB91CAT3, G	91C	77.8	5	86.5	91	95.5	1	125	4.8	0.106	120

4. A transient suppressor is normally selected according to the working peak reverse voltage (V<sub>RWM</sub>), which should be equal to or greater than the DC or continuous peak operating voltage level.

5. V<sub>BR</sub> measured at pulse test current I<sub>T</sub> at an ambient temperature of 25°C.

6. Surge current waveform per Figure 2 and derate per Figure 3 of the General Data – 600 Watt at the beginning of this group.

7. Bias Voltage = 0 V, F = 1 MHz, T<sub>J</sub> = 25°C

\*The "G" suffix indicates Pb-Free package available. Please refer back to Ordering Information on front page.

## P6SMB11CAT3 Series

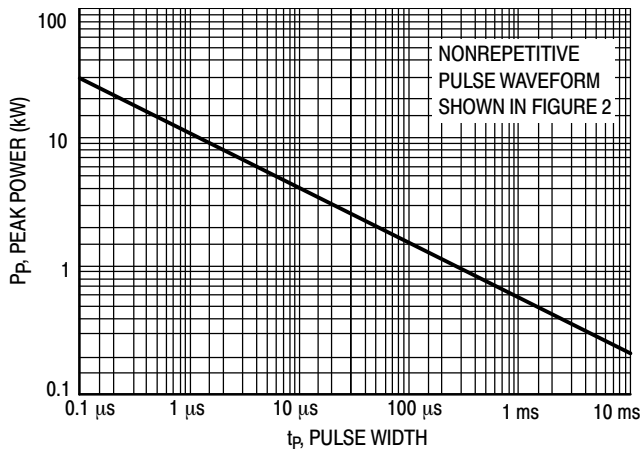


Figure 1. Pulse Rating Curve

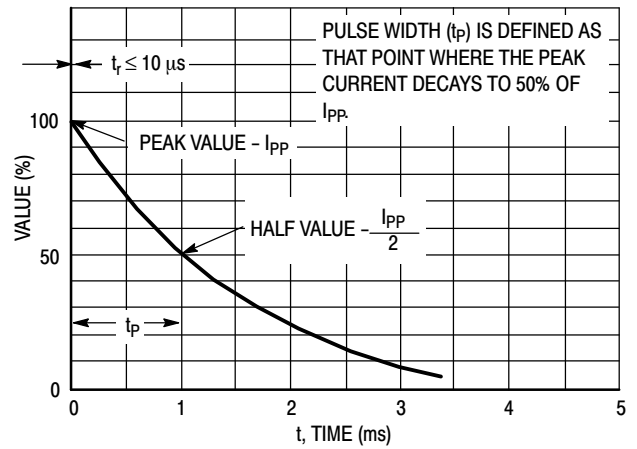


Figure 2. Pulse Waveform

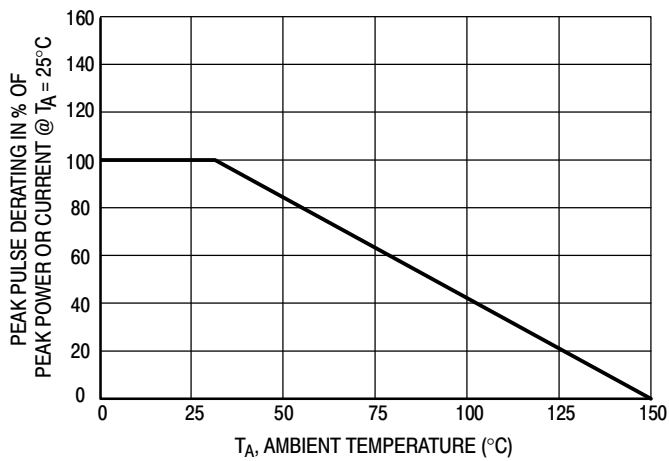


Figure 3. Pulse Derating Curve

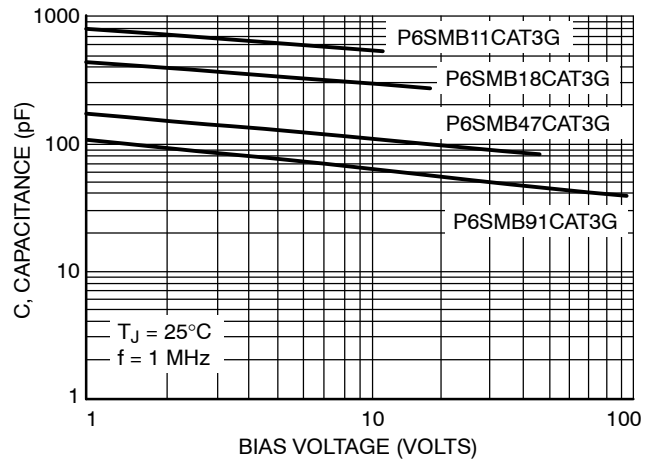
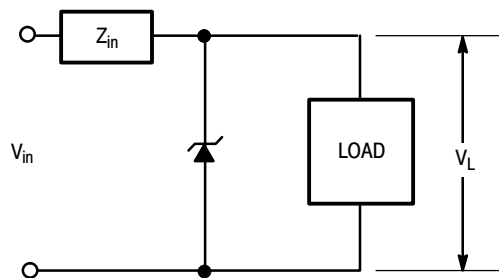


Figure 4. Typical Junction Capacitance vs. Bias Voltage

### TYPICAL PROTECTION CIRCUIT



## APPLICATION NOTES

### RESPONSE TIME

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitive effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure 4.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure 5. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. The SMB series have a very good response time, typically < 1 ns and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper circuit layout, minimum lead lengths and placing the

suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by  $Z_{in}$  is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

### DUTY CYCLE DERATING

The data of Figure 1 applies for non-repetitive conditions and at a lead temperature of 25°C. If the duty cycle increases, the peak power must be reduced as indicated by the curves of Figure 6. Average power must be derated as the lead or ambient temperature rises above 25°C. The average power derating curve normally given on data sheets may be normalized and used for this purpose.

At first glance the derating curves of Figure 6 appear to be in error as the 10 ms pulse has a higher derating factor than the 10  $\mu$ s pulse. However, when the derating factor for a given pulse of Figure 6 is multiplied by the peak power value of Figure 1 for the same pulse, the results follow the expected trend.

## P6SMB11CAT3 Series

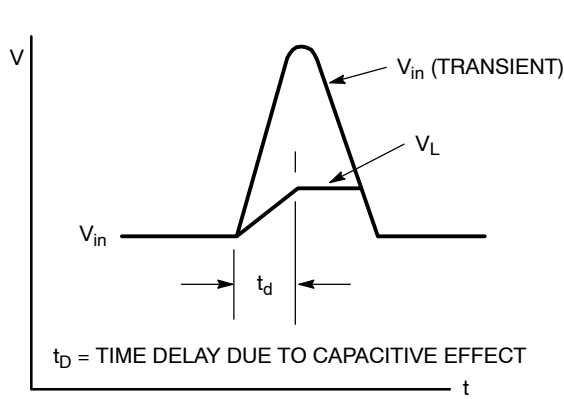


Figure 5.

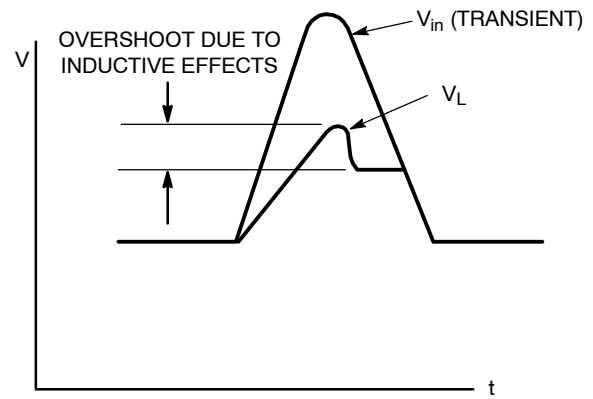


Figure 6.

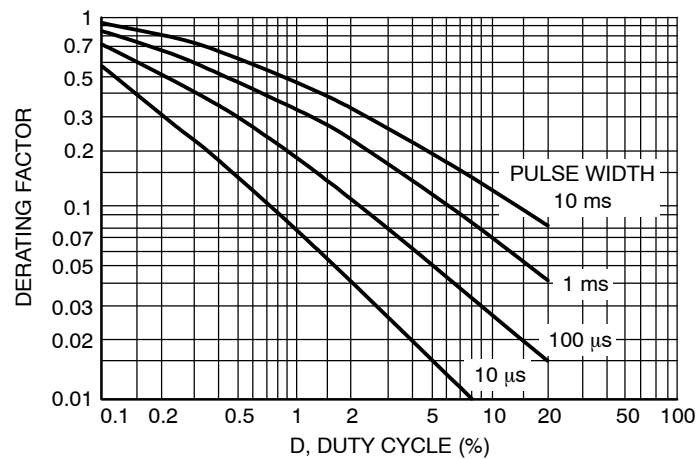


Figure 7. Typical Derating Factor for Duty Cycle

## UL RECOGNITION

The entire series has *Underwriters Laboratory Recognition* for the classification of protectors (QVGQ2) under the UL standard for safety 497B and File #E210057. Many competitors only have one or two devices recognized or have recognition in a non-protective category. Some competitors have no recognition at all. With the UL497B recognition, our parts successfully passed several tests

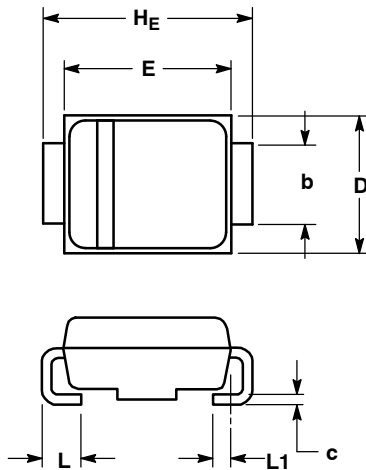
including Strike Voltage Breakdown test, Endurance Conditioning, Temperature test, Dielectric Voltage-Withstand test, Discharge test and several more.

Whereas, some competitors have only passed a flammability test for the package material, we have been recognized for much more to be included in their Protector category.

# P6SMB11CAT3 Series

## PACKAGE DIMENSIONS

### SMB DO-214AA CASE 403A-03 ISSUE F

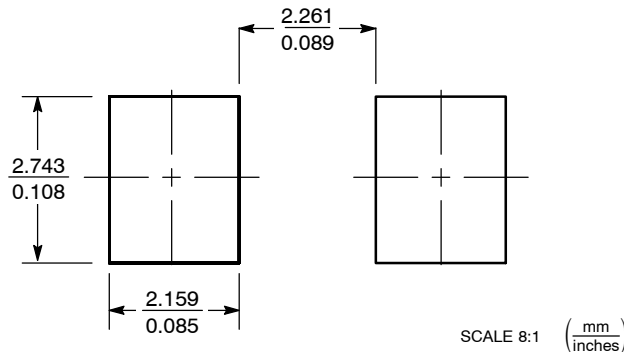


#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.90	2.13	2.45	0.075	0.084	0.096
A1	0.05	0.10	0.20	0.002	0.004	0.008
b	1.96	2.03	2.20	0.077	0.080	0.087
c	0.15	0.23	0.31	0.006	0.009	0.012
D	3.30	3.56	3.95	0.130	0.140	0.156
E	4.06	4.32	4.60	0.160	0.170	0.181
H_E	5.21	5.44	5.60	0.205	0.214	0.220
L	0.76	1.02	1.60	0.030	0.040	0.063
L1	0.51 REF			0.020 REF		


### SOLDERING FOOTPRINT\*



SCALE 8:1 (mm/inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SURMETIC is a trademark of Semiconductor Components Industries, LLC.

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### PUBLICATION ORDERING INFORMATION

**LITERATURE FULFILLMENT:**  
Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
Email: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5773-3850

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative

**P6SMB11CAT3/D**